

The Constituents of Semiconductor Components

Responsible electronic component and equipment manufacturers are already preparing for the time when the lifespan of their products comes to an end by scrutinizing the materials incorporated and their future recylcability. Recycling laws have already come into force in Germany ("Kreislauf-Wirtschaftsgesetz") and guidelines for electronic scrap are in preparation.

The aim is a suitable waste disposal program and – as a preventative measure – a reduction in the content of hazardous damaging materials in such components. In order to conform to this procedure, detailed information about the materials and their quantities is needed.

This overview answers questions put forward by customers as to the constituents and their function in the most important of Vishay Semiconductor's semiconductor products. Special significance is given to so-called "Hazardous Substances". It demonstrates that Vishay Semiconductor products under normal operating conditions do not expose the applier or environment to any hazard. However, most products nevertheless contain small but necessary quantities of "Hazardous Substances" which can – if not treated correctly or through accidents – be released on a small scale into the environment.

The present information was produced with the greatest possible care. Any suggestions for improvement of this brochure are welcome.

Definitions

Vishay Semiconductor offers a wide range of semiconductor components including transistors, diodes and opto-electronic components. These have been manufactured in various standard packages.

On the following pages, these packages are listed together with their materials shown in weight percentages. In order to limit the number of tables, all components whose structure and composition are the same have been compiled in families. In many cases, different lead frames together with chips of different sizes may be used for the one package. This usually means that there may be slight differences in the quantities of the declared material. The weight percent is, however, valid for a representative sample of the relevant family. In order to sensibly reduce the number and quantities of materials contained in the respective components, quantities smaller than 0.1% by weight have been stated in the following list as traces. This is the case unless lower limits are forced by law, e.g., cadmium < 75 ppm and PCDD as well as PCDF (known as dioxin) < 2 ppb. In the lists themselves,

details of content and composition are separated into the individual parts of the semiconductor component. The most important of these are:

Active element: The active element is either a silicon chip or for optoelectronic components a chip containing combinations of Ga (AI) (As, P). These are doped with very small amounts of boron, arsenic, phosphorus, zinc and germanium etc. The metallisation consists of thin layers of aluminium, gold or titanium. The chips are generally bonded to the lead frame with a silver epoxy and have gold or aluminium wires bonded to the lead frame.

Lead frame: For electrical connection, a metal lead frame made from alloys such as FeNi (42) or CuFe (2) and partly or totally plated with silver is commonly used. The metal alloys contain traces of silver, zinc and phosphorus. Part of the lead frame is also coated with tin/ lead.

Case: The semiconductor chip is protected from the environment by a case of glass, plastic or metal.

The glass is composed of oxides of silicon and lead together with boron and aluminium.

Plastic cases are composed of an epoxy resin filled with up to 70% by weight of quartz particles. Antimony trioxide and brominated epoxy resin (no TBA) are added as flame retardents. Antimony and bromine amount to about 1.6 and 1.0% respectively.

In use: In use, it is the content of hazardous substances which is of importance. In Germany, there are a series of lists which give the materials which are potentially hazardous to people and the environment, for example:

Appendix II and IV of the "Hazardous Materials Regulations", the TRGS 900 ("MAK-Wert-Liste") and the "Catalog of Materials Hazardous to the Water Supply". These lists, however, are only partially consistent.

The names used are often different for materials with the same chemical composition. Furthermore, the use of trivial and trade names often adds to the confusion.

Vishay Semiconductor therefore for their descriptions use that proposed by the Zentralverband Elektrotechnik und Elektronikindustrie e.V. (ZVEI; Central Association of Electrical Engineering and Electronic Industry) for the harmonization of the nomenclature of hazardous substances.

Statements are made on the safety precautions to be used during storage and disposal by mechanical, chemical and thermal means of the more important chemicals (so-called "Leitchemikalien"). These are listed in the tables in the order of their potential risk.



Their effect upon people and the environment are also listed and any special precautions emphasized.

Notes: The following information has been prepared to be as exact and reliable as possible.

The manufacture of semiconductor components is, however, subject to regular change without special notification.

The publication of this brochure excludes any responsibility resulting from its use.

Explanation of Abbreviations

While the information on weight percent is believed correct, discrepancies depending upon component type may be possible.

- 1) Material information etc. Material listed as "Material Hazardous in Production"
- S: Trace material < 0.1% by weight; Cd < 75 ppm; concerning Cd see ***)
 PCDD and PCDF < 2 ppb
- *) Dioxin content lies below agreed limits
- **) No. 85 "Rules for Hazardous Materials", to be replaced as soon as a technically suitable alternative material is available
- ***) Traces of cadmium can only be found in lead frames made of copper
- CMT: Material containing carcinogens, mutagens or terratogens
- Tox: Material is toxic or very toxic
- S Material with allergy producing characteristics
- HAL Halogen containing material
- WKG Material hazardous to the water supply
- L Storage, suitable for disposal
- D Disposable
- M Mechanical disposal
- N Chemical disposal
- T Thermal disposal
- H Handling

Ozone Depleting Substances

The use of Ozone Depleting Substances has been totally eliminated by Vishay Semiconductor and by doing so meets the legal requirements as defined in the following documents.

- 1. The "Montreal Protocol" together with the "London Amendments" Appendix A, B, and the "List of Transitional Substances"
- "Clean Air Act", Amendments 1990, "Environmental Protection Agency" (EPA), USA, Class I and II – Ozone Depleting Substances
- 3. "European Council Resolution" number 88/540/EEC and 91/690/eec Appendix A, B and C (Transitional Substances)

Vishay Semiconductor guarantees that its components do not contain and are manufactured without the use of Ozone Depleting Substances.



Table of Package Forms

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TDSG1150	6	TLHE5101	3
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TDSG3160	6	TLHE5800	3
TDSG5150	6	TLHF4200	5
TDSG5160	6	TLHF4600	5
TDSL1150	6	TLHF4900	5
TDSL1160	6	TLHF5400	3
TDSL3150	6	TLHF5800	3
TDSL3160	6	TLHG4200	5
TDSL5150	6	TLHG4201	5
TDSL5160	6	TLHG4205	5
TDSO1150	6	TLHG4400	5
TDSO1160	6	TLHG4401	5
TDSO3150	6	TLHG4405	5
TDSO3160	6	TLHG4600	5
TDSO5150	6	TLHG4601	5
TDSO5160	6	TLHG4605	5
TDSR1150	6	TLHG4900	5
TDSR1160	6	TLHG5100	3
TDSR3150	6	TLHG5101	3
TDSR3160	6	TLHG5102	3
TDSR5150	6	TLHG5200	3
TDSR5160	6	TLHG5201	3
TDSY1150	6	TLHG5205	3
TDSY3150	6	TLHG6200	3
TDSY3160	6	TLHG6201	3
TDSY5150	6	TLHG6205	3
TDSY5160	6	TLHG5400	3
TLBR5410	7	TLHG5401	3
TLDR4400	5	TLHG5405	3
TLDR4401	5	TLHG6400	3
TLDR4900	5	TLHG6401	3
TLDR4901	5	TLHG6405	3
TLDR5400	3	TLHG5800	3
TLDR5800	3	TLHK4200	5
TLHB4200	5	TLHK4400	5
TLHB4201	5	TLHK4600	5
TLHB4400	5	TLHK4900	5
TLHB4401	5	TLHK5100	3
TLHB5100	3	TLHK5100	3
	3	TLHK5101	3
TLHB5101			
TLHB5102	3	TLHK5400	3
TLHB5400	3	TLHK5800	3
TLHB5401	3	TLHO4200	5
TLHB5800	3	TLHO4201	5
TLHB5801	3	TLHO4400	5
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TLHE4400	5	TLHP4200	5
TLHE4600	5	TLHP4201	5
TLHE4900	5	TLHP4400	5
TLHE5100	5	TLHP4401	5



Part Number	Package Form	
TLHP4405	5	
TLHP4900	5	
TLHP5100	3	
TLHP5101	3	
TLHP5102	3	
TLHP5800	3	
TLHR4200	5	
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TLHR4205	5	
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TLHY6205	3	
TLHY6400	3	
TLHY6401	3	
TLHY6405	3	
TLHW5100	3	
TLHW5400		
1LHV0400	3	

Part Number TLLG4401 TLLG5400	Package Form 5
	5
TLLG5400	
	3
TLLG5401	3
TLLR4400	5
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TLMP3107	2
TLMT3100	2
TLMV3100	2
TLMY3100	2
TLMY3101	2
TLMY3102	2
TLMW3100	2
TLMW3101	2
TLMW3102	2



Part Number	Package Form
TLPG5600	9
TLPH5600	9
TLPP5600	9
TLPR5600	9
TLPY5600	9
TLRE4200	4
TLRG4400	4
TLRG4420	4
TLRH4400	4
TLRH4420	4
TLRO4400	4
TLRO4420	4
TLRP4400	4
TLRP4401	4
TLRP4406	4
TLRP4900	4
TLRY4220	4
TLRY4400	4
TLRY4420	4
TLSG2100	8
TLSG2101	8
TLSG5100	8
TLSG5101	8
TLSH2100	8
TLSH2101	8
TLSH5100	8
TLSH5101	8
TLSY2100	8
TLSY2101	8
TLSY5100	8
TLSY5101	8
TLSV5100	8
TLUG2400	4
TLUG2401	4

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TLUO2400	4
TLUO2401	4
TLUR2400	4
TLUR2401	4
TLUR4400	5
TLUR4401	5
TLUR5400	3
TLUR5400	3
TLUR6401	3
TLUR6401	3
TLUV5300	7
TLUY2400	4
TLUY2401	4
TLVB4200	5
TLVD4200	5
TLVG4200	5
TLVH4200	5
TLVH4201	5
TLVP4200	5
TLVS4200	5
TLVY4200	5
TLWR7600	1
TLWO7600	1
TLWY7600	1
TLWTG7600	1
TLWBG7600	1
TLWB7600	1
TLWW7600	1
TLWR7900	1
TLWO7900	1
TLWY7900	1
TLWTG7900	1
TLWBG7900	1
TLWB7900	1
TLWW7900	1



The Constituents of Package Forms

Package form 1:

					5 5	poxy resin (49%) 0% resin 0% hardener	Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg
					L 9 2 2 4 T	races of Fe, C, Cl ead frame Cu (50%) 2% copper % iron % silver % SnPb fraces of li, Zn, P, Cd ^{***)}	Silver epoxy (< 0.1%) 80% silver 10% resin 10% hardener Traces of CI, Na, K Silicone (< 1%) 90.9% resin 9.1% hardener
لاپ Total weight 280 mg						ED chip (< 0.1%) active Layers: (50%) aAsP, GaAlAs, GaP, aAsP, GaAlAs, GaP, aAN, InGaN, AlInGaP <u>bubstrates: (</u> 50%) aAP, GaAlAs, GaAs, biC fraces of au, Zn, Ge, Ti	YAG-Phosphor (< 0.1%) Y 25% Gd 44.3% Al ₂ , O ₃ , 30.7 Traces of Ce
Significant Materials for Disposal							
No. Material and/or Group ¹⁾	C M T	T O X	S	H A L	W G K	Available in the Compound Used for	Part in ²⁾ Weight Percent L D M N T H
1 Lead and lead compounds		•	-		•	Lead plating	0.1 • • •



Vishay Semiconductors

Package form 2:

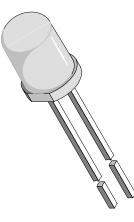
						5	Epoxy resin (10.0%) 50% resin 50% hardener	IR chip (0.17%) 50% gallium 50% arsenic
		>				6	Reflector (47.8%) 6.7%amodel	Traces of Al, Au, Zn, Ge, Ti
							33.3%glass fibre .ead frame (42.0%) 95% copper 1% iron 1% Silver % SnPb	Detector chip (0.2%) 99% silicon Traces of Ag, Al, Au, Sb, Ti, SiO ₂ Silver epoxy (< 0.1%) 80% silver
	Total weight 30 mg					Т	Traces of Ni, Zn, P, Cd ^{***)}	10% resin 10% hardener
						<u>A</u>	. ED chip (< 0.1%) A <u>ctive Layers:</u> (50%) BaAsP, GaAIAs, GaP, BaN, InGaN, AlInGaP	Traces of Cl, Na, K Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg
						S C T	<u>Substrates: (</u> 50%) GaP, GaAlAs, GaAs, Si Traces of Au, Zn, Ge, Ti	$\begin{array}{c} \textbf{YAG-Phosphor} \\ (< 0.1\%) \\ Y & 25\% \\ Gd & 44.3\% \\ Al_2, O_3, 30.7 \\ Traces of Ce \end{array}$
Sign	ificant Materials for Disposal							
No.	Material and/or Group ¹⁾	C M T	T O X	S	H A L	W G K	Available in the Compound Used for	Part in ²⁾ Weight Percent L D M N T H
1	Lead and lead compounds		•			٠	Lead plating	0.1 • • •



IR chip (0.1%) 50% gallium

50% arsenic

Package form 3:



Total weight (5 mm) 310 mg

Epoxy resin (58%) 50% resin 50% hardener Lead frame (42 %)

93% iron 2% copper 2% silver 3% SnPb Traces of Ni, Zn, P, Cd ^{***)}

LED chip (< 0.1%) Active Layers: (50%) GaAsP, GaAlAs, GaP, GaN, InGaN, AlInGaP <u>Substrates: (</u>50%) GaP, GaAlAs, GaAs, SiC Traces of Au, Zn, Ge, Ti Traces of Al, Au, Zn, Ge, Ti **Silicone** (< 1%) 90.9% resin 9.1% hardener **Silver epoxy** (< 0.1%) 80% silver 10% resin

10% hardener Bond wire (< 0.1%) 99.99% gold

Traces of BE, Mg

YAG-Phosphor (< 0.1%) Y 25% Gd 44.3% Al₂, O₃, 30.7 Traces of Ce

Significant Materials for Disposal

No. Material and/or Group ¹⁾	M	T O X	S	Α	G	Available in the Compound Used for	Part in ²⁾ Weight Percent ^L	DMNTH
1 Lead and lead compounds		٠			٠	Lead plating	0.1	• • •



Package form 4:



Total weight (3mm)132 mg

Significant Materials for Disposal

Epoxy resin (25%) 50% resin 50% hardener Traces of Fe, C, Cl

Lead frame (75%) 96% copper 2% iron 2% silver Traces of Ni, Zn, P, Cd^{***)}

LED chip (< 0.1%) Active Layers: (50%) GaAsP, GaAlAs, GaP, GaN, InGaN, AllnGaP <u>Substrates: (</u>50%) GaP, GaAlAs, GaAs, SiC Traces of Au, Zn, Ge, Ti Resistor chip (< 0.1%) 99% silicon Traces of Ag, Al, Au, Sb, Ti, B

Silver epoxy (< 0.1%) 80% silver 10% resin 10% hardener Traces of Cl, Na, K

Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg

No. Material and/or Group ¹⁾	C M T	0	Α	G	Available in the Compound Used for	Part in ²⁾ Weight Percent ^L	D MNTH
1 Lead and lead compounds		•		٠	Lead plating	0.1	• • •

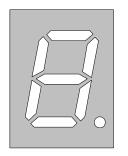


Package form 5:

		Epoxy resin (30%) 50% resin 50% hardener Traces of Fe, C, Cl Lead frame (70%) 90% iron 4% copper 2% silver 4% SnPb Traces of Ni, Zn, P, Cd ^{***})	LED chip (< 0.1%) <u>Active Layers:</u> (50%) GaAsP, GaAlAs, GaP, GaN, InGaN, AllnGaP <u>Substrates:</u> (50%) GaP, GaAlAs, GaAs, SiC Traces of Au, Zn, Ge, Ti IR chip (0.1%) 50% gallium 50% arsenic
		Silver epoxy (< 0.1%) 80% silver	Traces of Al, Au, Zn, Ge, Ti
		10% resin 10% hardener Traces of Cl, Na, K	Detector chip (< 0.1%) 99% silicon Traces of
Total weight (3mm) 130 mg		Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg	Ag, Al, Au, Sb, Ti, SiO ₂
Significant Materials for Disposal			
СТ	Н	W Available	Part in ²⁾

No.	Material and/or Group 1)	 ò	A	G	Available in the Compound Used for	Part in ²⁾ Weight Percent	LD	МИТН
1	Lead and lead compounds	•		•	Lead plating	0.1		• • •

Package form 6:



Case	Weight/ mg
7 mm	700
10 mm	1150
13 mm	2090

Epoxy resin (42.9%) 44.0%resin 48.0%hardener 8.0% diffuser

Reflector (39.8%) 73.0%Pocan 27.0%TiO₂

Lead frame (17.3%) 98.8%copper 1.2% iron Traces of Ni, Ag, Zn, Cd ^{***)}

Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg LED chip (< 0.1%) <u>Active Layers:</u> (50%) GaAsP, GaAlAs, GaP, GaN, InGaN, Alln-GaP <u>Substrates:</u> (50%) GaP, GaAlAs, GaAs, SiC Traces of Au, Zn, Ge, Ti Silver epoxy

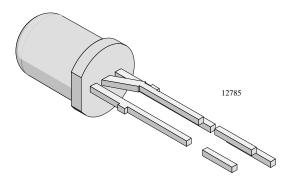
(< 0.1%) 80% silver 10% resin 10% hardener Traces of Cl, Na, K

Significant Materials for Disposal

No.	Material and/or Group ¹⁾		T O X	S	Α	G	Available in the Compound Used for	Part in ²⁾ Weight Percent ^L	D MNTH
1	Arsenic	٠	٠			٠	Chip	Traces	• • •
2	Epoxy resin						Mold	43.0	•



Package form 7:



Total weight 400 mg

Epoxy resin (50%) 50% resin 50% hardener Traces of Fe, C, Cl

Lead frame (50%) 96% copper 2% iron 2% silver Traces of Ni, Zn, P, Cd^{***)}

Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg

Silver epoxy (< 0.1%) 80% silver 10% resin 10% hardener

Traces of CI, Na, K

LED chip (< 0.1%) <u>Active Layers:</u> (50%) GaAsP, GaAlAs, GaP, GaN, InGaN, AlIn-GaP <u>Substrates:</u> (50%) GaP, GaAlAs, GaAs, SiC Traces of Au, Zn, Ge, Ti

Detector chip

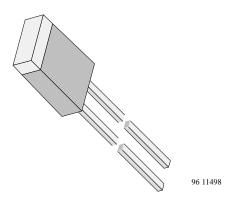
(< 0.1%) 99% silicon Traces of Ag, Al, Ni, Ti, V

Significant Materials for Disposal

No. Material and/or Group ¹⁾	C M T	0	Α	G	Available in the Compound Used for	Part in ²⁾ Weight Percent	L D	MNTH
1 Lead and lead compounds		•		٠	Lead plating	0.1		• • •



Package form 8:



approx. weight 300 mg

Epoxy resin (60%) 50% resin 50% hardener Traces of Fe, C, Cl

Lead frame (40%) 96% copper 2% iron 2% silver Traces of Ni, Zn, P, Cd^{***})

Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg

Detector chip (< 0.1%) 99% silicon Traces of Ag, Al, Ni, Ti, V LED chip (< 0.1%) <u>Active Layers:</u> (50%) GaAsP, GaAlAs, GaP, GaN, InGaN, Alln-GaP <u>Substrates:</u> (50%) GaP, GaAlAs, GaAs, SiC Traces of Au, Zn, Ge, Ti

Silver epoxy

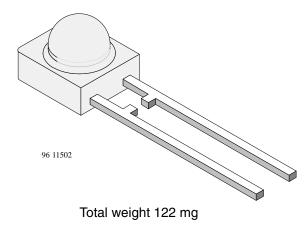
(< 0.1%) 80% silver 10% resin 10% hardener Traces of Cl, Na, K

Significant Materials for Disposal

No. Material and/or Group ¹⁾	C M T	Ó	Α	G	Available in the Compound Used for	Part in ²⁾ Weight Percent ^L	DMNTH
1 Lead and lead compounds		•		٠	Lead plating	0.1	• • •



Package form 9:



Epoxy resin (60%) 50% resin 50% hardener Traces of Fe, C, Cl

Lead frame (40%) 96% copper 2% iron 2% silver Traces of Ni, Zn, P, Cd^{***})

Bond wire (< 0.1%) 99.99% gold Traces of Be, Mg

Detector chip (< 0.1%) 99% silicon Traces of Ag, Al, Ni, Ti, V LED chip (< 0.1%) <u>Active Layers:</u> (50%) GaAsP, GaAlAs, GaP, GaN, InGaN, AlIn-GaP <u>Substrates:</u> (50%) GaP, GaAlAs, GaAs, SiC Traces of Au, Zn, Ge, Ti

Silver epoxy

(< 0.1%) 80% silver 10% resin 10% hardener Traces of Cl, Na, K

Significant Materials for Disposal

No.	Material and/or Group ¹⁾	C M T	Ó	S	Α	G	Available in the Compound Used for	Part in ²⁾ Weight Percent ^L	DMNTH
1	Lead and lead compounds		٠			•	Lead plating	0.1	• • •